

SOT23 NPN SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

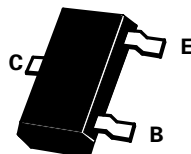
FMMT455

ISSUE 3 – FEBRUARY 1996

FEATURES

- * 140 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 500 mW

PARTMARKING DETAIL – 455



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	140	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	160		V	$I_C=100\mu\text{A}$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	140		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		0.1	μA	$V_{CB}=140\text{V}$
Emitter Cut-Off Current	I_{EBO}		0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.7	V	$I_C=150\text{mA}$, $I_B=15\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	100 10 Typ	300		$I_C=150\text{mA}$, $V_{CE}=10\text{V}^*$ $I_C=1\text{A}$, $V_{CE}=10\text{V}^*$
Transition Frequency	f_T	100		MHz	$I_C=50\text{mA}$, $V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		15	pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS

